



NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE1570 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

- V_{DS} =150V,I_D =70A
 R_{DS(ON)} <18mΩ @ V_{GS}=10V
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

- Power switching application
- Hard switched and High frequency circuits
- Uninterruptible power supply

100% UIS TESTED!

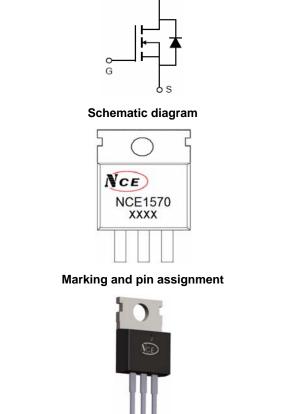
100% ΔVds TESTED!

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE1570	NCE1570	TO-220-3L	-	-	-

Absolute Maximum Ratings (T_c=25[°]C unless otherwise noted)

Limit	Unit
150	V
±20	V
70	А
49.5	А
280	А
310	W
2.07	W/℃
210	mJ
-55 To 175	°C
0.48	°C/W
-	310 2.07 210 55 To 175



TO-220-3L top view

D





Electrical Characteristics (T_c=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	·					
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	150	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =150V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250µA	2	3	4	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =20A	-	14	18	mΩ
Forward Transconductance	g fs	V _{DS} =5V,I _D =20A	50	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{lss}		-	6644	-	PF
Output Capacitance	C _{oss}	V_{DS} =75V, V_{GS} =0V,	-	243	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0MHz	-	178	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	28	-	nS
Turn-on Rise Time	tr	V_{DD} =75 V , R_L =15 Ω	-	30	-	nS
Turn-Off Delay Time	t _{d(off)}	V _{GS} =10V,R _G =2.5Ω	-	95	-	nS
Turn-Off Fall Time	t _f		-	40	-	nS
Total Gate Charge	Qg	N/ 75)// 00A	-	148.4		nC
Gate-Source Charge	Q _{gs}	$V_{DS}=75V, I_{D}=20A,$	-	28.4		nC
Gate-Drain Charge	Q _{gd}	V _{GS} =10V	-	49.8		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =20A	-		1.2	V
Diode Forward Current (Note 2)	I _S		-	-	70	A
Reverse Recovery Time	t _{rr}	TJ = 25°C, IF = 20A	-	40		nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs ^(Note3)	-	66		nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- **3.** Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production
- **5.** EAS condition: Tj=25 $^{\circ}$ C,V_{DD}=50V,V_G=10V,L=0.5mH,Rg=25 Ω

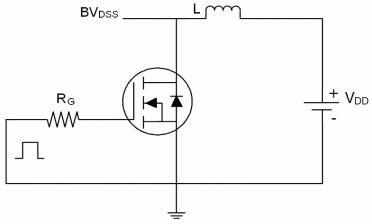


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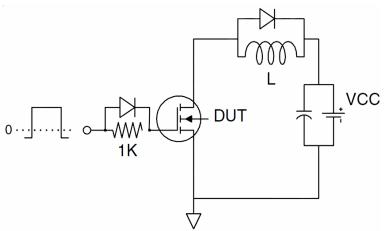




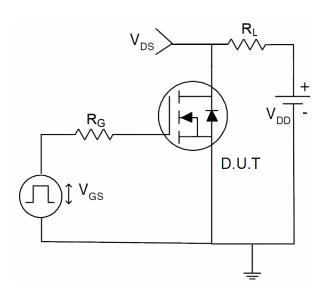
Test Circuit 1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit







75

75

100

25° С

0.8

1.0

0.6

125

150

175

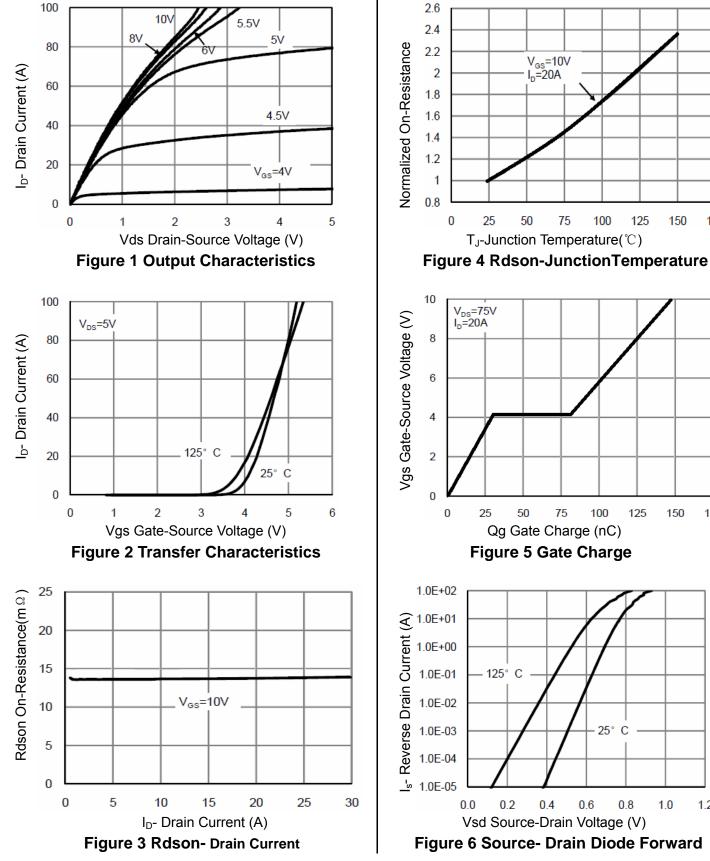
100

125

150

175





1.2



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NCE1570

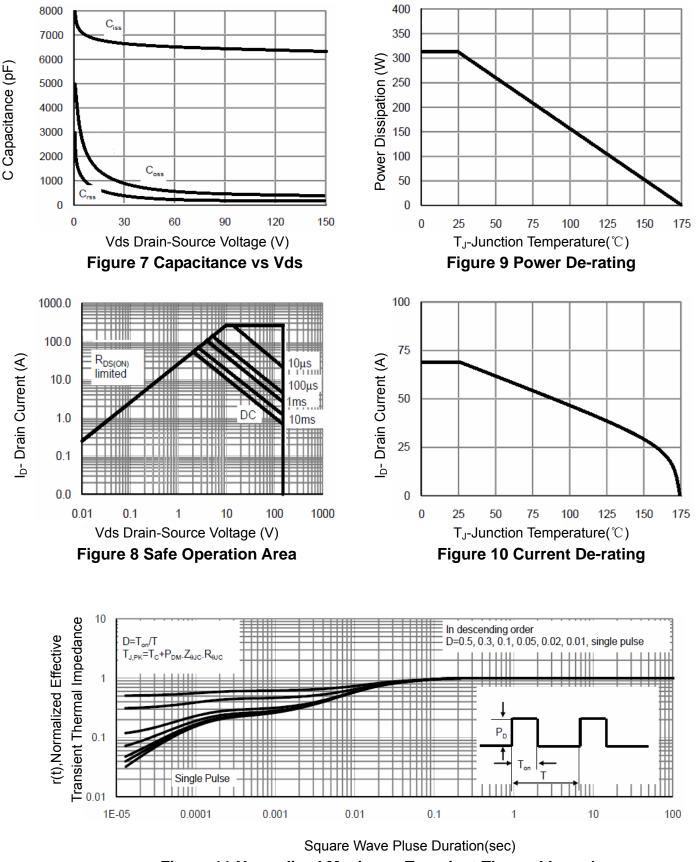


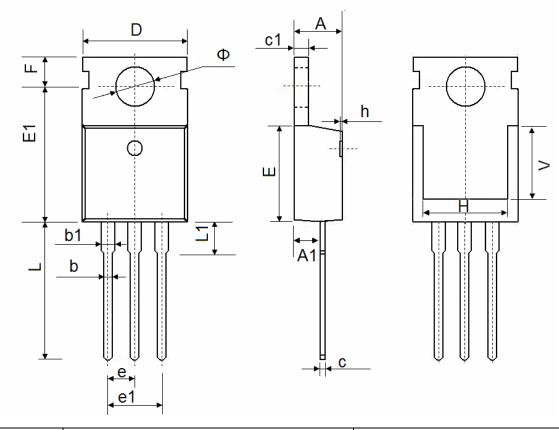
Figure 11 Normalized Maximum Transient Thermal Impedance



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TO-220-3L Package Information



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
	Min.	Max.	Min.	Max.	
А	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
E	8.9500	9.750	0.352	0.384	
E1	12.650	12.950	0.498	0.510	
е	2.540 TYP.		0.100 TYP.		
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	7.500 REF.		0.295 REF.		
Ф	3.400	3.800	0.134	0.150	







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